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Examiner J. J. Zimmerman	703 872-9019	Proposed Amendments for discussion at interview this afternoon

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Proposed New Claims A, B and C for Application No. 09/581,631 for discussion during
Interview on November 6, 2002

A. An electronic device comprising:
an electronic component having a first electrode; and
a second electrode formed on a circuit board, the first electrode and the second
electrode being electrically connected to each other, and bonded to each other with a
Pb-free solder, providing a connection between the first and second electrodes,
wherein the connection is made by contacting and soldering the Pb-free solder
with an electrode structure including the first electrode, the electrode structure
comprising the first electrode and a layered structure thereon consisting of an Sn-Bi
alloy layer containing 1-5 wt % Bi.

B. An electronic device comprising:
an electronic component having a first electrode; and
a second electrode provided on a circuit board on which the electronic
component is mounted, the first electrode and the second electrode being bonded to
each other by a Pb-free solder, providing a connection between the first and second
electrodes,
wherein the connection is made by contacting and soldering the Pb-free solder
with an electrode structure including the first electrode and a layered structure thereon
consisting of an Sn-Bi alloy layer containing 1-5 wt% Bi.

C. An electronic device comprising:
an electronic component having a first electrode; and
a second electrode formed on a circuit board, the first electrode and the second electrode being electrically connected to each other, and bonded to each other with a Pb-free solder, providing a connection between the first and second electrodes,
wherein the connection is made by contacting and soldering the Pb-free solder with an electrode structure including the first electrode and a layered structure thereon consisting of an Sn-Bi alloy layer containing 1-5 wt% Bi.

Proposed amendments to claims 43, 50, 51 and 59 of Application No. 09/972,178 for discussion during interview on November 6, 2002

43. (Amended) An electronic device which comprises a first electrode provided on an electronic component and a second electrode formed on a circuit board, the both electrodes being electrically connected with each other by means of a [solder] solder-containing portion, wherein an Sn-Bi alloy layer containing 1 to 5 wt% Bi is on the first electrode and the Sn-Bi alloy layer is in contact with [solder] solder-containing portion [of] from a Pb-free alloy, and the [solder] solder-containing portion is in contact with the second electrode.

50. (Amended) An electronic device which comprises a first electrode provided on an electronic component and a second electrode provided on a circuit board on which the electronic component is mounted, the both electrodes being bonded with each other by means of a solder, wherein an Sn-Bi alloy layer containing 1 to 5 wt% Bi is [adjacent] in contact with the first electrode as a surface layer, and the Sn-Bi alloy layer is in contact with [the solder] a solder bonding portion made [of] from Pb-free alloy, and the solder bonding portion is in contact with the second electrode.

51. (Amended) An electronic device which comprises an electronic component having a first electrode with an Sn-Bi alloy layer, a circuit board with a second electrode, and a bonding part [of] formed from a Pb-free solder which bonds the first electrode and the second electrode to each other, wherein the Sn-

Bi alloy layer contains 1 to 5 wt% Bi and is on the first electrode, and the [Pb-free solder] bonding part is in contact with the second electrode.

59. (Amended) An electronic device which comprises a semiconductor provided with a first electrode and a second electrode formed on a circuit board, the both electrodes being electrically connected with each other by means of a solder, wherein an Sn-Bi alloy layer containing 1 to 5 wt% Bi is [adjacent] in contact with the first electrode as a surface layer, and the Sn-Bi alloy layer is in contact with the solder bonding portion, made [of] from a Pb-free alloy, and the solder bonding portion is in contact with the second electrode.

Proposed amendments to claims 1, 12, 17 and 23 of Application
No. 10/183,897 for discussion during interview on November 6, 2002

1. (Amended) A semiconductor device with a lead which is made from a lead frame, wherein the lead has [an] a layered structure thereon which consists of a single Sn-Bi alloy layer, comprising 1 to 5 wt% Bi, thereon.

12. (Amended) A semiconductor device with a lead which is made from a lead frame, wherein [an] a layered structure which consists of a single Sn-Bi alloy layer, which comprises from 1 to 5 wt% Bi, is formed on the lead.

17. (Amended) A semiconductor device with a lead which is made from a lead frame, wherein [an] a layered structure which consists of a single Sn-Bi alloy layer, which comprises from 1 to 5% Bi, is formed directly on the lead.

23. (Amended) A semiconductor device with a lead which is made from a lead frame, wherein an Sn-Bi alloy layer, which comprises from 1 to 5 wt% Bi, is formed directly on the lead as a surface layer.